

**Amendments to the Specification:**

On page 1, please replace paragraph [0002] with the following amended paragraph:

*approved*  
*Lee*  
*12/20/05*

Referring generally to ~~Fig. 1~~ Figs. 1a-1e, shallow trench isolation (STI) is an enabling technology for the fabrication of advanced sub-micron integrated devices. A typical STI process sequence includes the following process steps: pad oxide oxidation, LPCVD nitride deposition, trench lithography, trench etch, resist strip/clean, liner oxidation, CVD oxide trench fill, planarization, post-chemical mechanical polishing (CMP) clean/light BHF dip, and nitride strip. This sequence describes STI related processes only and leaves out many other front-end processing steps.

On page 2, please replace paragraph [0005] with the following amended paragraph:

~~Fig. 1~~ Figs. 1a-1e ~~is~~ are side planar views in cutaway of a typical STI fabrication sequence[[:]].

On page 2, please replace paragraph [0006] with the following amended paragraph:

Fig. 2 is a top view of an exemplary set of test regions and a test area, and,